# **Hex Inverter**

# (Unbuffered)

The MC74LVX04 is an advanced high speed CMOS unbuffered hex inverter. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

#### **Features**

- High Speed:  $t_{PD} = 4.1 \text{ ns (Typ)}$  at  $V_{CC} = 3.3 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 2 \mu A \text{ (Max)}$  at  $T_A = 25 \text{°C}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Low Noise:  $V_{OLP} = 0.5 \text{ V (Max)}$
- Pin and Function Compatible with Other Standard Logic Families
- These Devices are Pb-Free and are RoHS Compliant



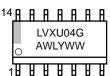
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**MARKING DIAGRAMS** 



SOIC-14 **D SUFFIX** CASE 751A

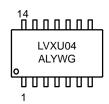




TSSOP-14 **DT SUFFIX CASE 948G** 







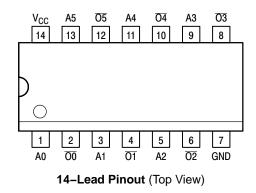
LVXU04 = Specific Device Code = Assembly Location

WL, L = Wafer Lot = Year WW. W = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.



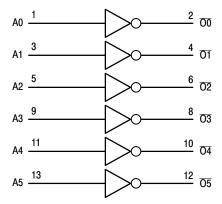


Figure 1. Logic Diagram

## **PIN NAMES**

Pins	Function
An	Data Inputs
On	Outputs

## **FUNCTION TABLE**

An	On
L	H
H	L

## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74LVXU04DG	SOIC-14 (Pb-Free)	55 Units / Rail
MC74LVXU04DR2G	SOIC-14 (Pb-Free)	2500 Tape & Reel
MC74LVXU04DTG	TSSOP-14 (Pb-Free)	96 Units / Rail
MC74LVXU04DTR2G	TSSOP-14 2500 Tape & Reel (Pb-Free)	
MC74LVXU04MG	SOEIAJ-14 (Pb-Free)	50 Units / Rail

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
\*This package is inherently Pb–Free.

#### **MAXIMUM RATINGS**

Symbol	Р	arameter	Value	Unit
$V_{CC}$	DC Supply Voltage		-0.5 to +7.0	V
V <sub>IN</sub>	DC Input Voltage		-0.5  to  +7.0	V
V <sub>OUT</sub>	DC Output Voltage		$-0.5$ to $V_{CC} + 0.5$	V
I <sub>IK</sub>	DC Input Diode Current	V <sub>I</sub> < GND	-20	mA
I <sub>OK</sub>	DC Output Diode Current	±20	mA	
I <sub>OUT</sub>	DC Output Sink Current		±25	mA
I <sub>CC</sub>	DC Supply Current per Supply Pin		±50	mA
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 1	0 Seconds	260	°C
TJ	Junction Temperature under Bias		+150	°C
$\theta_{\sf JA}$	Thermal Resistance	SOIC TSSOP	250	°C/W
P <sub>D</sub>	Power Dissipation in Still Air at 85°C	SOIC TSSOP	250	mW
MSL	Moisture Sensitivity		Level 1	
F <sub>R</sub>	Flammability Rating	Oxygen Index: 30% – 35%	UL 94-V0 @ 0.125 in	
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 1) Machine Model (Note 2) Charged Device Model (Note 3)	> 2000 > 200 2000	V
I <sub>Latchup</sub>	Latchup Performance	Above V <sub>CC</sub> and Below GND at 85°C (Note 4)	±300	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Tested to EIA/JESD22-A114-A.
- 2. Tested to EIA/JESD22-A115-A.
- 3. Tested to JESD22-C101-A.
- 4. Tested to EIA/JESD78.

### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	Supply Voltage	2.0	3.6	V
VI	Input Voltage (Note 5)	0	5.5	V
Vo	Output Voltage (HIGH or LOW State)	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Free–Air Temperature	-40	+ 85	°C
Δt/ΔV	Input Transition Rise or Fall Rate $V_{CC} = 3.0 \text{ V} \pm 0.3 \text{ V}$	0	100	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

5. Unused inputs may not be left open. All inputs must be tied to a high- or low-logic input voltage level.

#### DC ELECTRICAL CHARACTERISTICS

			V <sub>CC</sub> T <sub>A</sub> =		T <sub>A</sub> = 25°C		$T_A = -40$	to 85°C	
Symbol	Parameter	Test Conditions	v	Min	Тур	Max	Min	Max	Unit
V <sub>IH</sub>	High-Level Input Voltage		2.0 3.0 3.6	1.5 2.0 2.4			1.5 2.0 2.4		V
V <sub>IL</sub>	Low-Level Input Voltage		2.0 3.0 3.6			0.5 0.8 0.8		0.5 0.8 0.8	V
V <sub>OH</sub>	High-Level Output Voltage (V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub> )	$I_{OH} = -50 \mu A$ $I_{OH} = -50 \mu A$ $I_{OH} = -4 \text{ mA}$	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		V
V <sub>OL</sub>	Low–Level Output Voltage (V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub> )	I <sub>OL</sub> = 50 μA I <sub>OL</sub> = 50 μA I <sub>OL</sub> = 4 mA	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44	V
I <sub>in</sub>	Input Leakage Current	V <sub>in</sub> = 5.5 V or GND	3.6			±0.1		±1.0	μΑ
Icc	Quiescent Supply Current	V <sub>in</sub> = V <sub>CC</sub> or GND	3.6			2.0		20.0	μΑ

## AC ELECTRICAL CHARACTERISTICS (Input $t_f = t_f = 3.0 \text{ns}$ )

			$T_A = 25^{\circ}C$ $T_A = -40 \text{ to } 85^{\circ}C$		T <sub>A</sub> = 25°C				
Symbol	Parameter	Test Cond	itions	Min	Тур	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation Delay, Input to Output	V <sub>CC</sub> = 2.7V	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		5.4 7.9	10.1 13.6	1.0 1.0	12.5 16.0	ns
		$V_{CC} = 3.3 \pm 0.3 V$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		4.1 6.6	6.2 9.7	1.0 1.0	7.5 11.0	
t <sub>OSHL</sub>	Output-to-Output Skew (Note 6)	$V_{CC} = 2.7V$ $V_{CC} = 3.3 \pm 0.3V$	$C_L = 50 \text{ pF}$ $C_L = 50 \text{ pF}$			1.5 1.5		1.5 1.5	ns

Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t<sub>OSHL</sub>) or LOW-to-HIGH (t<sub>OSLH</sub>); parameter guaranteed by design.

#### **CAPACITIVE CHARACTERISTICS**

		T <sub>A</sub> = 25°C		T <sub>A</sub> = -40 to 85°C			
Symbol	Parameter	Min	Тур	Max	Min	Max	Unit
Cin	Input Capacitance		4	10		10	pF
C <sub>PD</sub>	Power Dissipation Capacitance (Note 7)		18				pF

<sup>7.</sup> C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:  $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}/6$  (per buffer). C<sub>PD</sub> is used to determine the no–load dynamic power consumption;  $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$ .

## **NOISE CHARACTERISTICS** (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 3.3$ V, Measured in SOIC Package)

		T <sub>A</sub> = 25°C		
Symbol	Characteristic	Тур	Max	Unit
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	0.3	0.5	V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	-0.3	-0.5	V
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage		2.0	V
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage		0.8	V

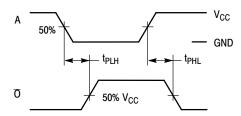
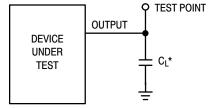


Figure 2. Switching Waveforms

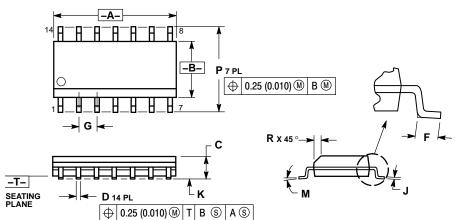


\*Includes all probe and jig capacitance

Figure 3. Test Circuit

#### **PACKAGE DIMENSIONS**

## SOIC-14 **D SUFFIX** CASE 751A-03 **ISSUE J**

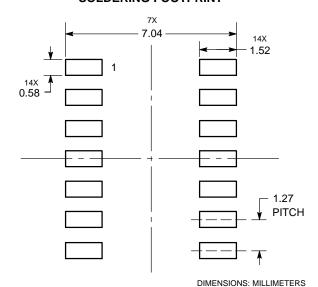


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
   CONTROLLING DIMENSION: MILLIMETER.
   DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
   MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
   DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION: ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

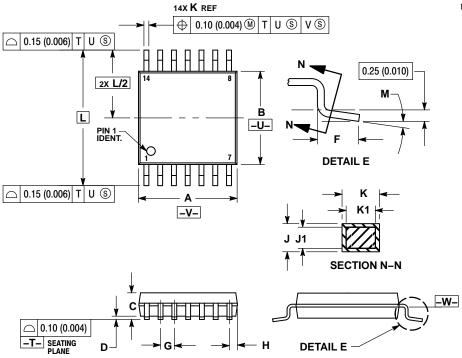
	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
М	0°	7°	0 °	7°
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

## **SOLDERING FOOTPRINT**



#### PACKAGE DIMENSIONS

#### TSSOP-14 **DT SUFFIX** CASE 948G **ISSUE B**



- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

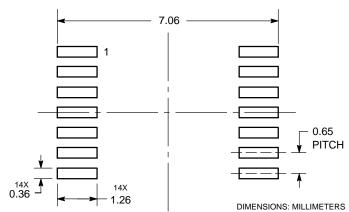
  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. CONDITION.
  6. TERMINAL NUMBERS ARE SHOWN FOR

  - 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

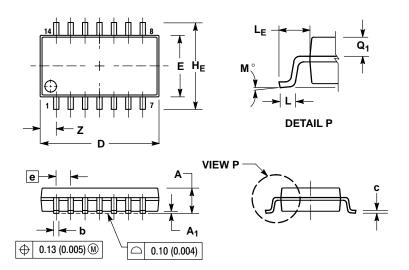
	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40		0.252 BSC		
М	0 °	8°	0 °	8 °	

#### **SOLDERING FOOTPRINT**



#### PACKAGE DIMENSIONS

SOEIAJ-14 **M SUFFIX CASE 965 ISSUE B** 



#### NOTES

- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.
- B. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

  TERMINAL NUMBERS ARE SHOWN FOR
- B. ILEMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

  5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION.

  DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.10	0.20	0.004	0.008
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050	BSC
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10°
Q <sub>1</sub>	0.70	0.90	0.028	0.035
Z		1.42		0.056

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